

**Amendments to the Specification:**

Please add the following new paragraphs [0065] and [0066] after paragraph [0064] and renumber subsequent paragraphs accordingly:

**[0065]** Figure 5 shows an optoelectronic device 401 produced by an embodiment of the method of the present invention. Device 401 may include a substrate 410, a first electrode 420, a wetting layer 425, a first layer 430, a second layer 440, a planarizing layer 445, and a second electrode 450. This figure is not necessarily drawn to scale. For example, although the bulk heterojunction which is formed by the interface of the second layer 440 on the first layer 430 is represented by a solid line in Figure 5, the bulk heterojunction is more accurately depicted by the schematic diagram of Figure 1(b). A representative embodiment of the device 401 includes an anode as the first electrode 420, an electron donor layer as the first layer 430, an electron acceptor layer as the second layer 440, and a cathode as the second electrode 450. Another representative embodiment of the device 401 includes a cathode as the first electrode 420, an electron acceptor layer as the first layer 430, an electron donor layer as the second layer 440, and an anode as the second electrode 450.

**[0066]** Figure 6 shows an optoelectronic device 402 produced by an embodiment of the method of the present invention. Device 402 may include a substrate 410, a first electrode 420, a first layer 430, a second layer 440, an electron-hole recombination zone 444, a third layer 446, a fourth layer 448, and a second electrode 450. This figure is not necessarily drawn to scale. For example, although the bulk heterojunction which is formed by the interface of the second layer 440 on the first layer 430 is represented by a solid line in Figure 6, the bulk heterojunction is more accurately depicted by the schematic diagram of Figure 1(b). A representative embodiment of the device 402 includes an anode as the first electrode 420, an electron donor layer as the third layer 446, an electron acceptor layer as the fourth layer 448, and a cathode as the second electrode 450. Another representative embodiment of the device 402 includes a cathode as the first electrode 420, an electron acceptor layer as the third layer 446, an electron donor layer as the fourth layer 448, and an anode as the second electrode 450.